

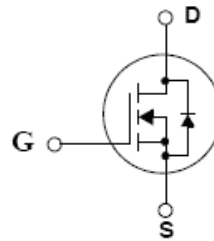
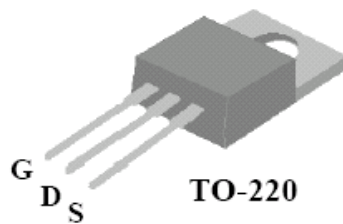
1 Description

These N-Channel enhancement mode power field effect transistors are produced using planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

2 Features

- 60V / 84A
- $R_{DS(on)} = 9m\Omega(\text{typ}) \cdot V_{GS} = 10V, I_D = 42A$
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability..



3 Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	APQ84SN06AH-XXM0	Units
		APQ84SN06AH-XXJ0	
		TO-220	
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	84	A
		50.4	A
I_{DM}	Drain Current – Pulsed ①	336	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy ②	320	mJ
I_{AR}	Avalanche Current	50	A
E_{AR}	Repetitive Avalanche Energy	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - De-rate above 25°C	100	W
		0.8	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	soldering temperature for 10 seconds	300	$^\circ\text{C}$

* note :

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 30V$, starting $T_J = 25^\circ\text{C}$, $L = \text{TBD}$, $R_G = 0\Omega$, $I_{AS} = 84A$
- ③ $I_{SD} \leq 84A$, $di/dt \leq 100A/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.



DEVICE SPECIFICATION

APQ84SN06AH

60V/84A N-Channel MOSFET

4 Thermal Characteristics

Symbol	Parameter	APQ84SN06AH-XXM0		Units
		APQ84SN06AH-XXJ0		
		TO-220		
		Typ.	Max.	
R _{θJC}	Thermal Resistance, Junction-to-Case	--	1.25	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

5 Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	60	--	--	V
I _{DSS}	Gate to Source leakage current	V _{DS} = 60 V, V _{GS} = 0 V	--	--	25	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 42 A ④	--	9	12	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 32.5 A ①	69	--	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 30 V, V _{GS} = 0 V, f = 1.0 MHz	--	3200	--	pF
C _{oss}	Output Capacitance		--	687	--	pF
C _{rss}	Reverse Transfer Capacitance		--	135	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 30A, R _G = 4.7 Ω, R _D = 1 Ω V _{GS} = 10V ④	--	11	--	ns
t _r	Turn-On Rise Time		--	75	--	ns
t _{d(off)}	Turn-Off Delay Time		--	45	--	ns
t _f	Turn-Off Fall Time		--	50	--	ns
Q _g	Total Gate Charge	V _{DS} = 30 V, I _D = 30A, V _{GS} = 10 V ④	--	--	125	nC
Q _{gs}	Gate-Source Charge		--	--	25	nC
Q _{gd}	Gate-Drain Charge		--	--	40	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	84	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	336	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 25 A	--	--	1.5	V



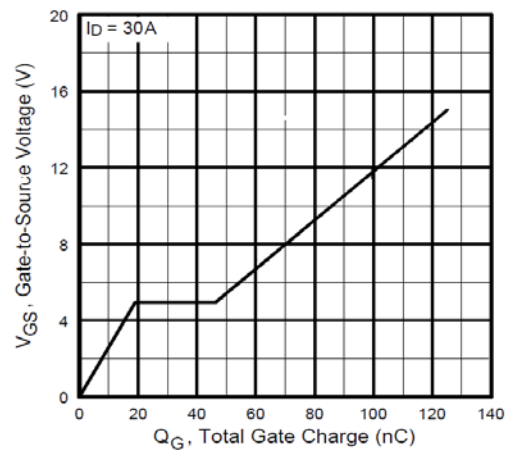
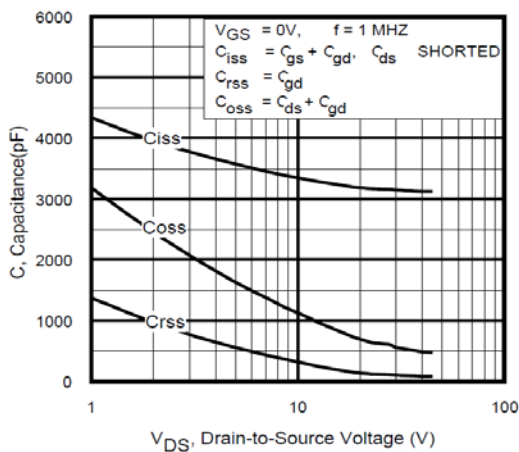
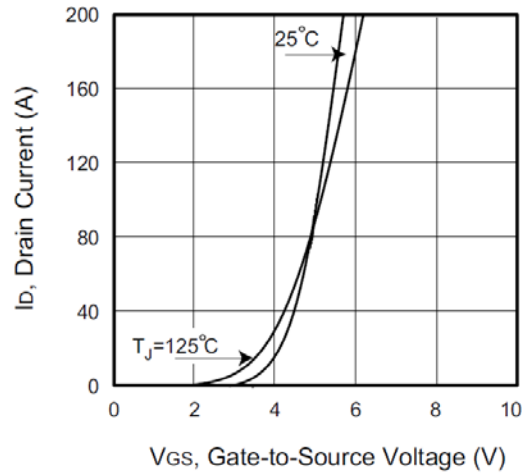
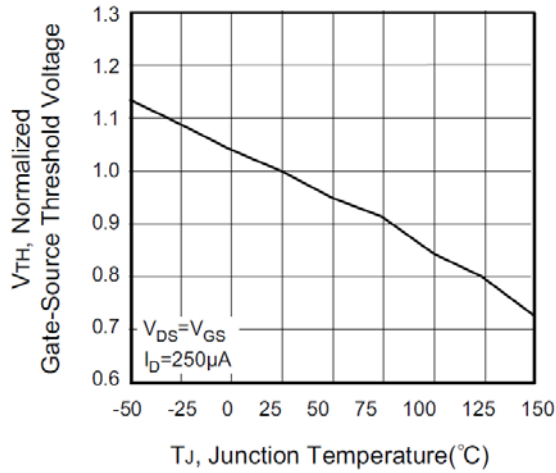
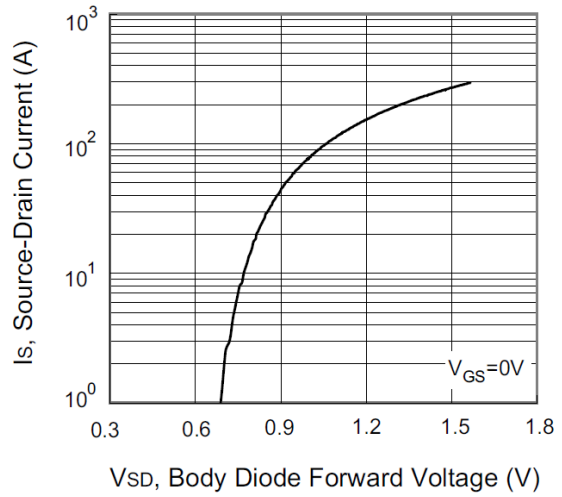
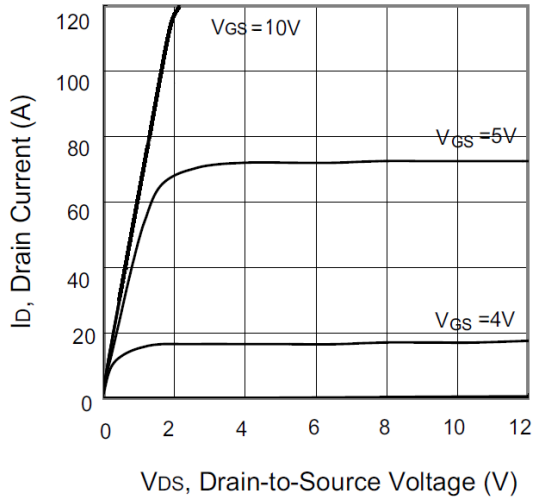
DEVICE SPECIFICATION

APQ84SN06AH

60V/84A N-Channel MOSFET

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② $V_{DD}=30V$, starting $T_J=25^{\circ}C$, $L=TBD$, $R_G=0\Omega$, $I_{AS}=84A$
- ③ $I_{SD} \leq 84A$, $di/dt \leq 100A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^{\circ}C$
- ④ Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$. Depend on FT Test.
- ⑤ CP Test

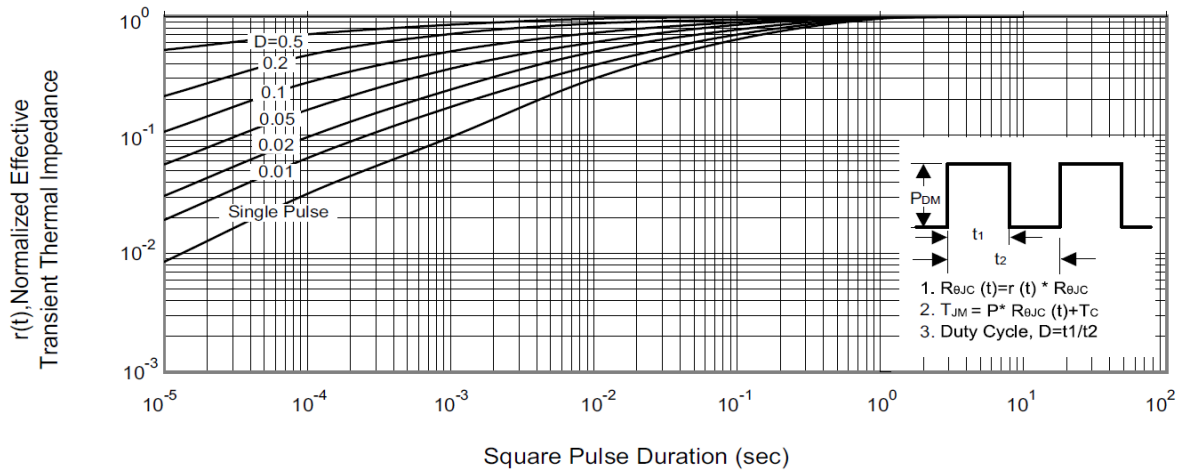
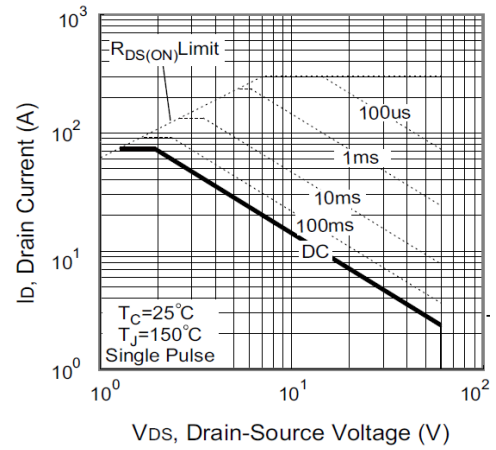
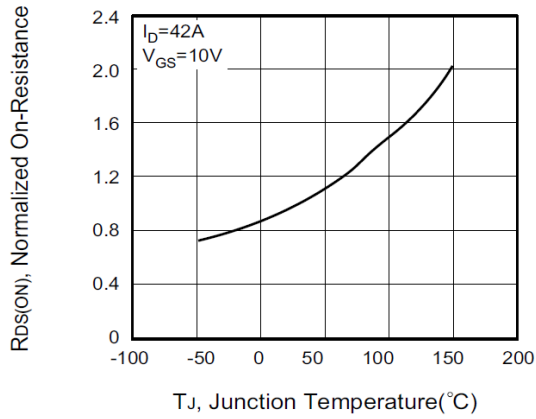




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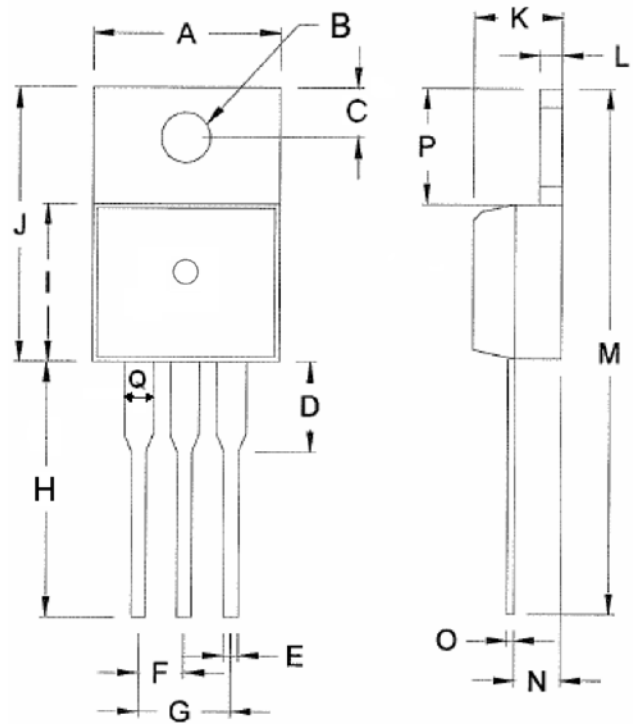
60V/84A N-Channel MOSFET



6 Package Dimensions

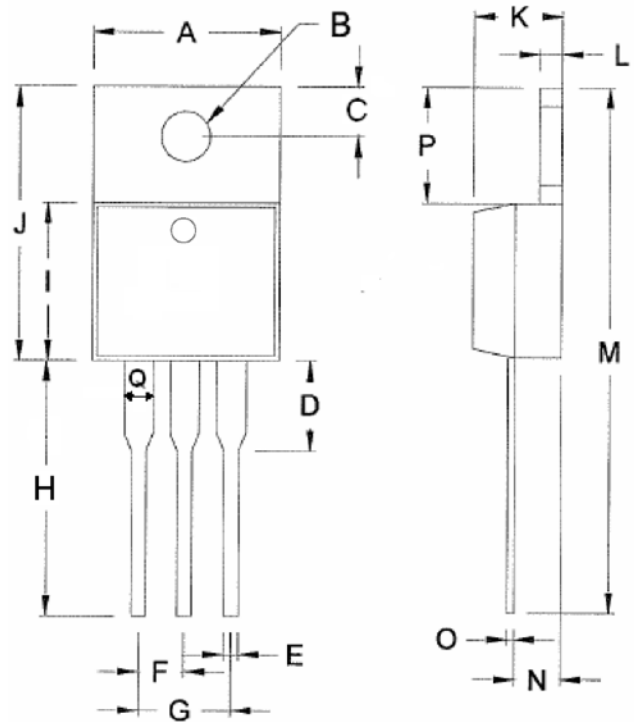
APQ84SN06AH-XXM0 TO-220

TO-220 DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	10.04	10.41	10.23
B	3.66	3.88	3.77
C	2.50	2.84	2.67
D	3.31	4.50	3.91
E	0.70	0.91	0.81
F	2.54(typ.)		2.54
G	5.08(typ.)		5.08
H	13.47	14.20	13.84
I	8.50	9.00	8.80
J	14.80	15.49	15.15
K	4.32	4.57	4.45
L	1.22	1.42	1.30
M	28.27	29.69	28.98
N	2.40	2.90	2.65
O	0.36	0.53	0.45
P	5.97	6.47	6.22
Q	1.15	1.45	1.30



APQ84SN06AH-XXJ0
TO-220

TO-220 DIMENSION			
DIM	MILLIMETERS		
	MIN	MAX	TYP.
A	10.01	10.31	10.16
B	3.66	3.94	3.80
C	2.59	2.89	2.74
D	3.5	3.96	3.73
E	0.70	0.90	0.80
F	2.54 TYP.		
G	4.98	5.18	5.08
H	13.4	13.8	13.6
I	8.5	8.9	8.70
J	14.65	15.35	15.05
K	4.47	4.67	4.57
L	1.22	1.42	1.32
M	28.05	29.15	28.60
N	2.52	2.82	2.67
O	0.31	0.53	0.42
P	6.10	6.50	6.30
Q	1.17	1.37	1.27





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60V/84A N-Channel MOSFET

Note

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